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## SPECTROSCOPIC ANALYSIS OF PLASMA ETCHING

 $\mathbf{B}\mathbf{y}$ 

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## Abstract

The emission spectra of  $\mathrm{CF_4-O_2}$  discharges during etching of silicon and silicon dioxide are examined in order to indicate the end-point of the process. This method is used to study the mechanism of plasma etching, too. Results are explained by use of thermochemical data.